

# Geothermal Power Plays

High Temperature Electronics for Downhole Environments  
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Dallas, Texas  
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SALES & MARKETING

# Agenda:

- > Introduction
- > Given
- > Goals
- > High Temperature
- > Applications
- > Focus – High Temperature Artificial Lift
- > High Temperature Electronics for Downhole Environments
- > HT Solutions
  - > Components & Sub-Systems
  - > Engineering Services & Turn-Key Systems
- > Conclusion

# Joule's Niche:



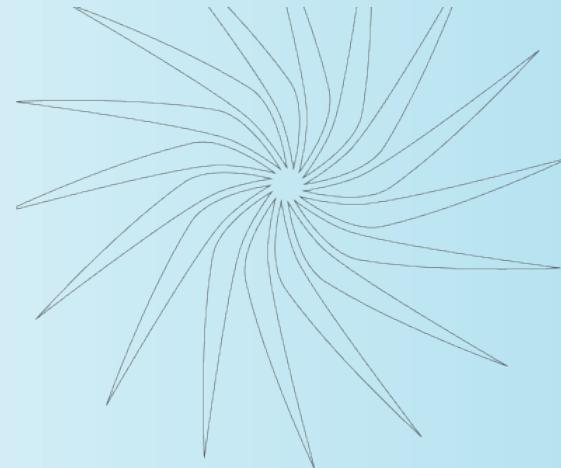
Joule is a contracted sales representative of high temperature suppliers. We represent suppliers of components, sub-systems, design and contract engineering services, specified to operate in high reliability or extreme temperature environments.

Our vertical market strategy and experience makes Joule a valued resource to both Customers, and Suppliers.

# Markets Served:

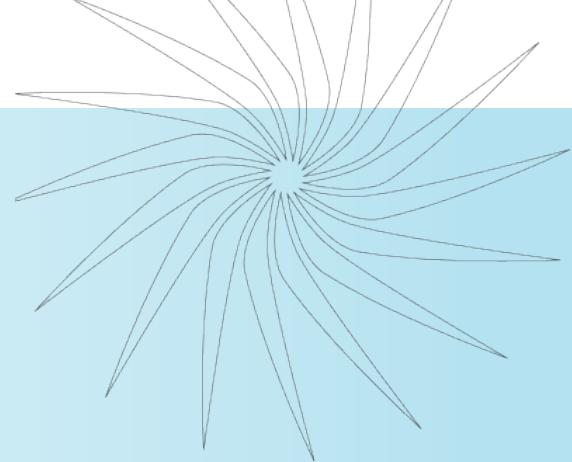
## Current Market Engagements:

- > Oil and Gas
- > Military and Aerospace
- > Semiconductor
- > Geothermal Energy



## Emerging Target Markets :

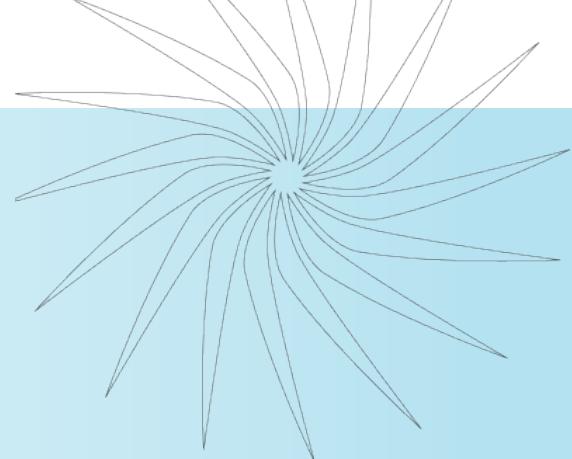
- > Military Automotive
- > Solar and Wind Energy



# Geothermal Power Plays

**High Temperature Electronics for  
Downhole Environments**

# Given:



Geothermal drilling, formation evaluation, and downhole monitoring is the most challenging with hottest and hardest demanding conditions.

This environment severely limits the life and performance of electronic components, subsystems, and turn-key designs.

Given:

## LEVELIZED COST OF ELECTRICITY LCOE Formula

$$\text{LCOE} = \frac{\sum_{t=1}^n \frac{I_t + M_t + F_t}{(1+r)^t}}{\sum_{t=1}^n \frac{E_t}{(1+r)^t}}$$

$I_t$  = investment expenditures in the year t;  $M_t$  = O&M expenditures in the year t;  $F_t$  = fuel expenditures in the year

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**Et = electricity generation in the year**

# Presentation Goals:

- > Provide an overview of electronic components, sub-systems, tools and engineering services available today for high temperature downhole applications.
- > Specifically target increasing the rates of flow, and overall improvements in artificial lift.
- > Identify companies / entities with specific high temperature interest and determine contacts to engage with.



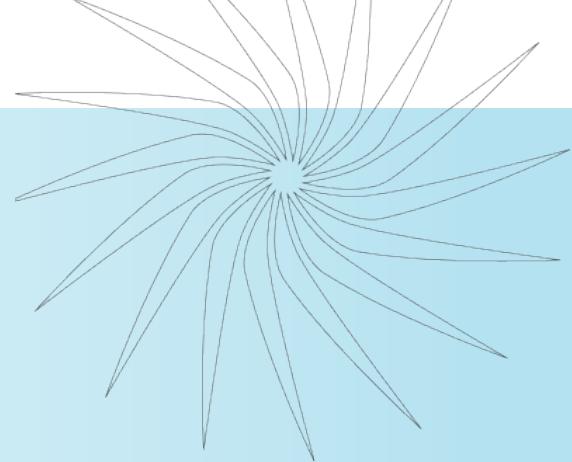
HOW MUCH WORK IS REQUIRED TO MOVE A UNIT OF ENERGY:

# High Temperature:

The definition of high temperature is application specific.

For our discussion today we will focus on:

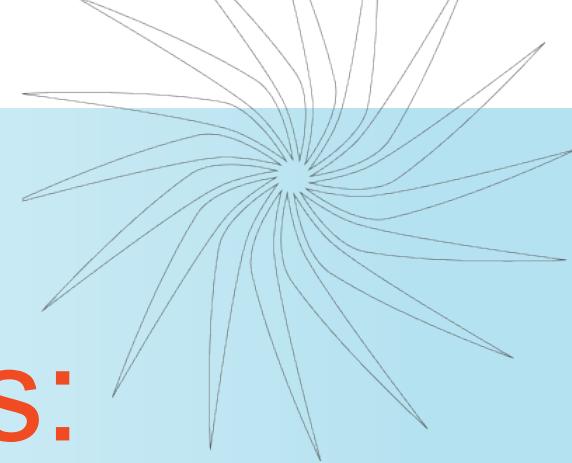
**Geothermal EGS**  
**Typical 200°C - 300°C**



# **Applications**

## **High Temperature Electronics for Downhole Environments**

# High Temperature Downhole Disciplines:



Drilling and Measurement  
Formation Evaluation  
Intervention  
Completions  
Production



# Common DHT Applications for Components and Sub-systems:

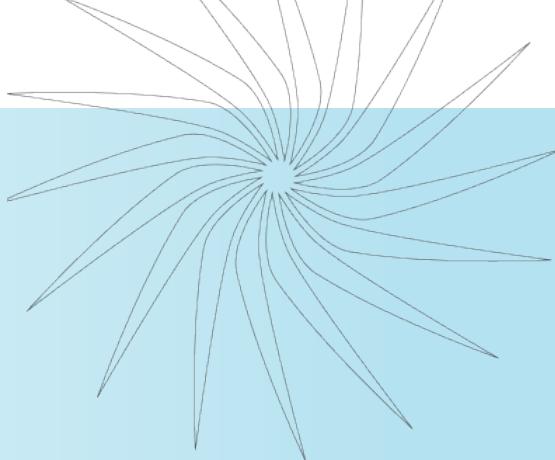


- > Energy Storage
- > Actuation
- > Power Conversion / Inversion
- > Voltage Regulation
- > Gate Drive / Motor Drive / Motor Control
- > Data Acquisition / Communication / Storage
- > Well Monitors
- > Artificial Lift - ESP

When your application needs the hottest solution .

# EGS 230°C Artificial Lift

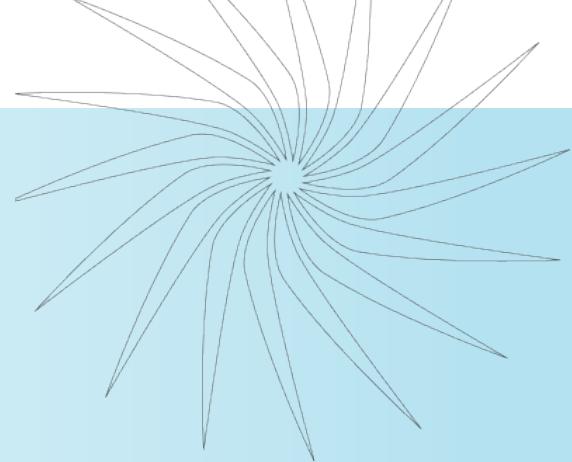
## (Currently not available)



A MIT panel in the “Future of Geothermal Energy” noted that it is critical to develop a production flow rate of 80 kg/sec at 200°C well head temperature to make EGS systems viable.

ONE kind of artificial lift appears applicable for geothermal EGS systems; Electrical Submersible Pumps (ESP)

- > ESPs have higher potential for reaching EGS optimal production
- > Biggest and highest temperature ESP should be used
- > Conduct HALT and HT Aging to predict EOL

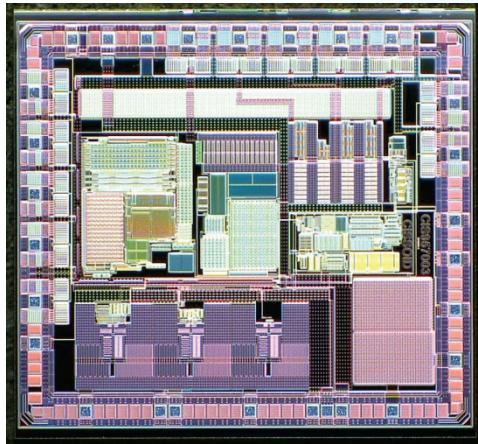


# High Temperature Electronics for Downhole Environments Applications

# High Temperature Silicon Components

- > Some Silicon based devices may support operation to:
  - > ~ 190 - 200°C with appropriate high temperature packaging
- > T<sub>j</sub> and thermal shutdown are common limiting factors
- > Die availability is usually limited
  - > Minimum Order Quantities (MOQ) of wafers required
  - > May be cost prohibitive for low volume usage
- > Die requires HT packaging
- > Silicon based components should be used if functionality cannot be found in SOI, SiC or GaN technologies
  - > HT Characterization & Aging is required for critical mission profiles
- > Recommend - HT Ceramic Packaging / Flask Technology
  - > Contracting experienced HT Design Teams

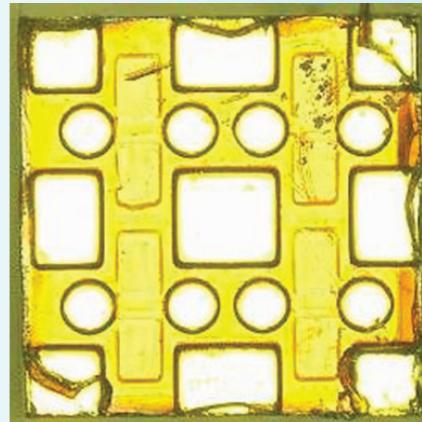
# HT Semiconductors which can be used for Geothermal Applications



## HTSOI

High temperature silicon on insulator devices rated to 230 °C and operable to 300 °C. Devices include Gate Drive, MOSFETS, 555 timers, voltage regulators, microcontrollers, op-amps, logic, ADCs, etc...

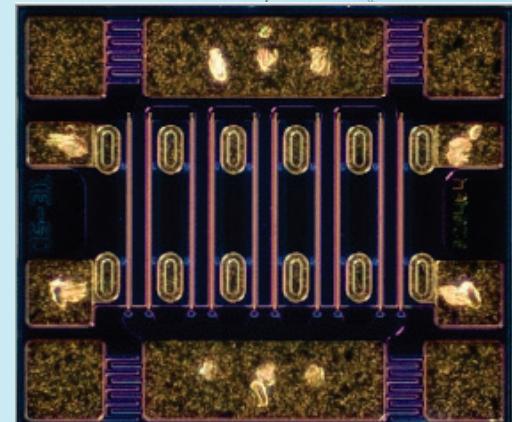
AVAILABLE TODAY



## SiC

Silicon Carbide devices have been field tested to temperatures in excess of 550 °C, with some literature reporting transistor operation up to 650 °C, and SiC ICs have been demonstrated

AVAILABLE TODAY



## GaN

Gallium Nitride devices are mainly discrete transistors, which have been shown to operate up to 600 °C, with a theoretical operating temperature higher than SiC

NEW TECHNOLOGY

# X-Rel Semiconductor

## SOI Reliability Assessment

- > Devices are set at still 250°C (case temperature) on an application board with dynamic bias conditions.
- > Permanent operation monitoring is carried out, though only total failure is detected here.
- > Parts are pulled out of the aging fixture at given schedule to be tested according to the standard test program at 25°C and 220°C. Pull Schedule is: once every 4wk. Results for each device are logged to show any possible drift.
- > Two golden (not aged) parts are used to monitor test fixture dependence.
- > Over 100,000 Hours at 250C for some devices to date

# High Temp Components:

## EVANS CAPACITOR 200 °C

>High Temperature High Energy Hybrid Tantalum Capacitors

## APEI 225 °C

>Silicon Carbide MOSFETS and GaN Power Modules  
>H Bridge, Motor Driver and Gate Drive Solutions

## SPJ Thick Film RESISTORS 300 °C

>High Temperature, High Precision Wire Wound and Thick Film

## UNITED SILICON CARBIDE 260 °C

>High Temperature, Highly Efficient Diodes, JFETs and Cascode Switches

## VECTRON INTERNATIONAL 230 °C

>High Temperature Crystals and Oscillators

## VANGUARD ELECTRONICS 220 °C

> High Temperature Magnetics - Transformers, Inductors & Chokes

## X-REL SEMICONDUCTOR 230 °C

>High Temperature, Power Regulation, PWM and DC to DC Converters  
>High temperature Gate Driver chipsets

## CRITERIA LABS HT DIE PACKAGING 230 °C

>High Temperature packaging / Component Characterization & Aging

# High Temperature Sub-Systems And Design Services

Very Little “Off the Shelf” solutions exist above 175°C

- > IR              SOI DC to DC Power Modules
- > APEI          Gate Driver, Motor Driver & Power Conversion

200°C + solutions are application specific.

- > For high temperature contract engineering we need an agreed upon specific Statement of Work (SOW), complete with mission/test profile and a prototype acceptance document to begin design.

# High Temp Solutions >175C

## PERMAWORKS\* 300°C

- > Reservoir Testing and Monitoring {PW-PT535A} High Temperature, High Reliability tool designed for and delivers reservoir stimulation and well shut in testing visibility.

## FASTCAP ASYSTEMS\* 150°/200°C

- > High Temperature Ultra Capacitor
- > High Temperature Battery Systems

## TI 210°C

- > MCU, OP Amps, Power Analog, Signal Conversion

## ADI 200°C

- > OP Amps, Signal Conversion

## REL-CHIP\* 300°C

- > High Temperature 32-Bit MCU, Memory

## CREE / ROHM / INFINEON\* 175°C

- > High Temperature, SiC Diodes and MOSFETs

## VECTRON INTERNATIONAL 180°C

- > Real-time Clock Module

## HDA\* 200°C

- > High Temperature Memory

## CRITERIA LABS HT DIE PACAKGING 230°C

- > SOI/ SiC Motor Driver & DC to DC

# Joule Design Services:

## CAPACITOR MODULES 200°C

>HP/HT High Energy Hybrid Tantalum Capacitors Modules

## POWER SUPPLIES 200°C

>Low and High Voltage Power Supplies 1W – 100KW

## SOI DATA ACQUISITION 225°C

>High Pressure, Strain and High Temperature Data Acquisition  
>Position Sensing

## SILICON CARBIDE POWER MODULES 260°C

>High Temperature, High Power Energy Conversion, Gate Driver and Motor Drivers

## REAL-TIME CLOCK MODULES 180°C

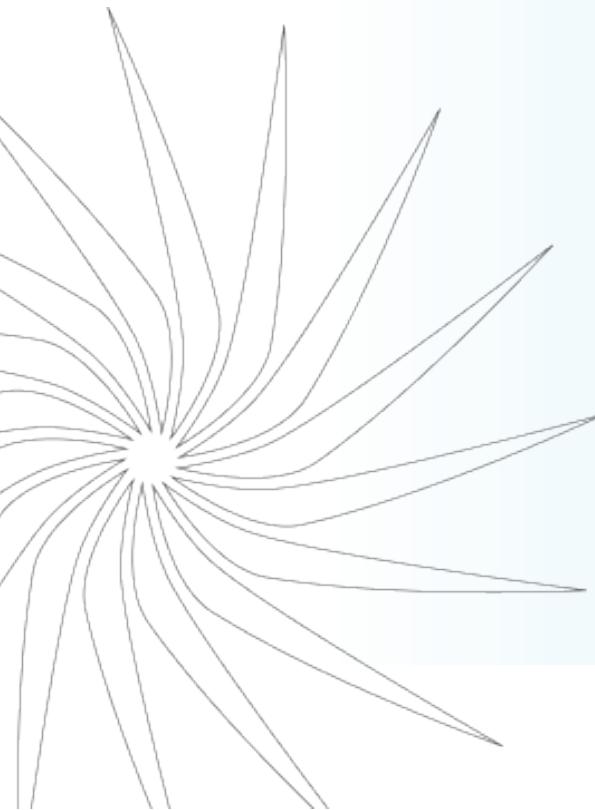
## CUSTOM MAGNETICS 220°C

## HIGH TEMPERATURE CHARACTERIZATION/AGING 230°C

## DIE, MCM AND HYBRID PACKAGING 240°C

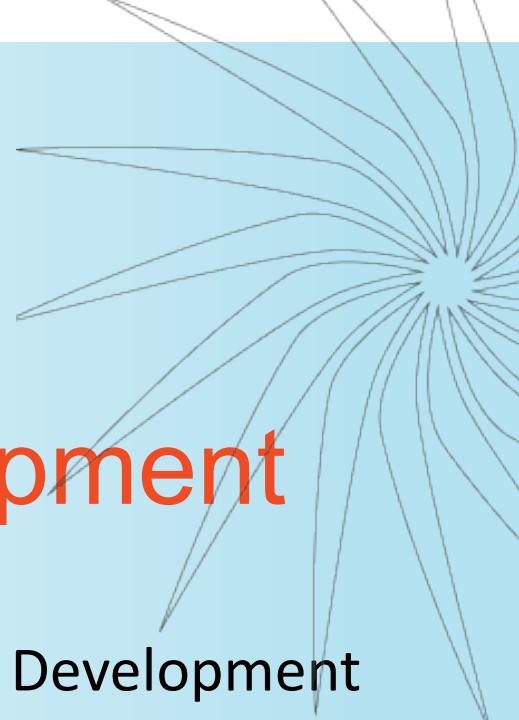
## DOWNHOLE & SURFACE ELECTRICAL AND MECHANICAL ENGINEERING SERVICES -40°C to 230°C

>Application Specific Design Services



# Conclusion

## Cost-competitive energy requires technology development



- > Investment in High Temperature Research & Development
  - >DoD , DoE , DoT & NASA
  - >Continued support of National Laboratories
- > Private initiative creating innovation in technologies
  - >Government and Corporate sponsorships
- > Production process improvements – ESP
- > Utilization of HT downhole technologies and experience
- > HT Characterization, aging and deployment

Thank you.

Joule

Fueling Next Generation Design,  
Delivering Innovative High Temp Solutions.